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SHEET 1 OF 1

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 212771US22PCT		SERIAL NO. 09/926,186	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Masashi KAWASAKI, et al.			
				FILING DATE September 20, 2001		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>SJR</i>	AA	5,530,267	06/25/96	C. D. BRANDLE, JR., et al. (submitting corr. JP 8-288220 only)			
<i>SJR</i>	AB	6,057,561	05/02/2000	M. KAWASAKI, et al.			
	AC						
	AD						
	AE						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
<i>SJR</i>	AF	0 863 555	09/09/98	EUROPE (submitting corr. JP 10-256673 and JP 10-270749 only)			
<i>SJR</i>	AG	8-288220	11/01/96	JAPAN			X
<i>SJR</i>	AH	10-256673	09/25/98	JAPAN			X
<i>SJR</i>	AI	10-270749	10/09/98	JAPAN			X
	AJ						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>SJR</i>	AK	N. KIMIZUKA, et al., Journal of Solid State Chemistry, vol. 78, pages 98-107, "STRUCTURAL CLASSIFICATION OF $\text{RAO}_3(\text{MO})_n$ COMPOUNDS (R = Sc, In, Y, OR LANTHANIDES; A = Fe(III), Ga, Cr, OR Al; M = DIVALENT CATION; n = 1-11)", 1989					
<i>SJR</i>	AL	N. KIMIZUKA, et al., Journal of Solid State Chemistry, vol. 74, pages 98-109, "HOMOLOGOUS COMPOUNDS, $\text{InFeO}_3(\text{ZnO})_m$ (m = 1-9)", 1988					
<i>SJR</i>	AM	J. KOIKE, et al., Jpn. J. Appl. Phys., vol. 34, no. 5B, pages 2678-2682, "QUASI-MICROWAVE BAND LONGITUDINALLY COUPLED SURFACE ACOUSTIC WAVE RESONATOR FILTERS USING $\text{ZnO}/\text{SAPPHIRE}$ SUBSTRATE", 1995					
<i>SJR</i>	AN	A. OHTOMO, et al., Applied Physics Letters, vol. 75, no. 17, pages 2635-2637, "SINGLE CRYSTALLINE ZnO FILMS GROWN ON LATTICE-MATCHED $\text{ScAlMgO}_4(0001)$ ", October 25, 1999.					
<i>SJR</i>	AO	C.D. BRANDLE, et al., Solid-State Electronics, vol. 41, no. 12, pages 1943-1945, "STABILITY OF HYDROGEN IN ScAlMgO_4 ", 1997					
<i>SJR</i>	AP	E. S. HELLMAN, et al., 3 pages, " ScAlMgO_4 : AN OXIDE SUBSTRATE FOR GaN EPITAXY"					
	AQ	E. S. HELLMAN, et al., MRS Internet Journal of Nitride Semiconductor Research, vol. 1, Article 1, "ScAlMgO_4: AN OXIDE SUBSTRATE FOR GaN EPITAXY", January 16, 1996					
Examiner <i>Shawn...</i>					Date Considered <i>6/6/03</i>		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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